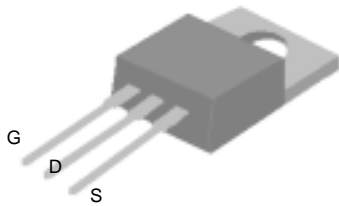


N-channel Enhancement-mode Power MOSFET

PRODUCT SUMMARY

BV_{DSS}	200V
$R_{DS(ON)}$	400m Ω
I_D	9A

 **Pb-free; RoHS-compliant TO-220**



TO-220 (suffix P)

DESCRIPTION

The SSM630GP achieves fast switching performance with low gate charge without a complex drive circuit. It is suitable for low voltage applications such as DC/DC converters and general load-switching circuits.

The SSM630GP is in TO-220 for through-hole mounting where a small footprint is required on the board, and/or an external heatsink is to be attached.

These devices are manufactured with an advanced process, providing improved on-resistance and switching performance.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Units
V_{DS}	Drain-source voltage	200	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Continuous drain current, $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	9	A
		5.7	A
I_{DM}	Pulsed drain current ¹	36	A
P_D	Total power dissipation, $T_C = 25^\circ\text{C}$	74	W
	Linear derating factor	0.59	W/ $^\circ\text{C}$
E_{AS}	Single pulse avalanche energy ³	240	mJ
I_{AR}	Avalanche current	9	A
E_{AR}	Repetitive avalanche energy	7	mJ
T_{STG}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range	-55 to 150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Maximum thermal resistance, junction-case	1.7	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Maximum thermal resistance, junction-ambient	62	$^\circ\text{C}/\text{W}$

Notes:

1. Pulse width must be limited to avoid exceeding the safe operating area.
2. Pulse width <300us, duty cycle <2%.
3. Starting $T_J = 25^\circ\text{C}$, $V_{DD} = 50\text{V}$, $L = 4.5\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 9\text{A}$.

ELECTRICAL CHARACTERISTICS (at $T_j = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown voltage temperature coefficient	Reference to 25°C , $I_D=1\text{mA}$	-	0.248	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static drain-source on-resistance	$V_{GS}=10V, I_D=5A$	-	-	400	$\text{m}\Omega$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward transconductance	$V_{DS}=10V, I_D=5A$	-	40	-	S
I_{DSS}	Drain-source leakage current	$V_{DS}=200V, V_{GS}=0V$ $V_{DS}=160V, V_{GS}=0V, T_j = 150^\circ\text{C}$	-	-	10 25	μA μA
I_{GSS}	Gate-source leakage current	$V_{GS}=\pm 30V$	-	-	± 100	nA
Q_g	Total gate charge ²	$I_D=9A$	-	25	-	nC
Q_{gs}	Gate-source charge	$V_{DS}=160V$	-	3.6	-	nC
Q_{gd}	Gate-drain ("Miller") charge	$V_{GS}=10V$	-	14	-	nC
$t_{d(on)}$	Turn-on delay time ²	$V_{DS}=100V$	-	8	-	ns
t_r	Rise time	$I_D=9A$	-	26	-	ns
$t_{d(off)}$	Turn-off delay time	$R_G=10\Omega, V_{GS}=10V$	-	34	-	ns
t_f	Fall time	$R_D=11\Omega$	-	22	-	ns
C_{iss}	Input capacitance	$V_{GS}=0V$	-	515	-	pF
C_{oss}	Output capacitance	$V_{DS}=25V$	-	90	-	pF
C_{rss}	Reverse transfer capacitance	$f=1.0\text{MHz}$	-	40	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward voltage ²	$I_S=9A, V_{GS}=0V$	-	-	1.3	V
I_S	Continuous source current (body diode)	$V_D=V_G=0V, V_S=1.3V$	-	-	36	A
I_{SM}	Pulsed source current (body diode) ¹		-	-	9	A

Notes:

1. Pulse width must be limited to avoid exceeding the maximum junction temperature of 150°C .

2. Pulse width $<300\mu s$, duty cycle $<2\%$.

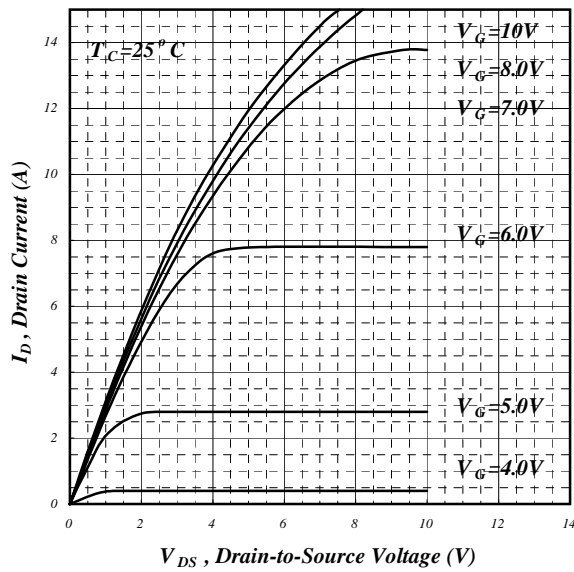


Fig 1. Typical Output Characteristics

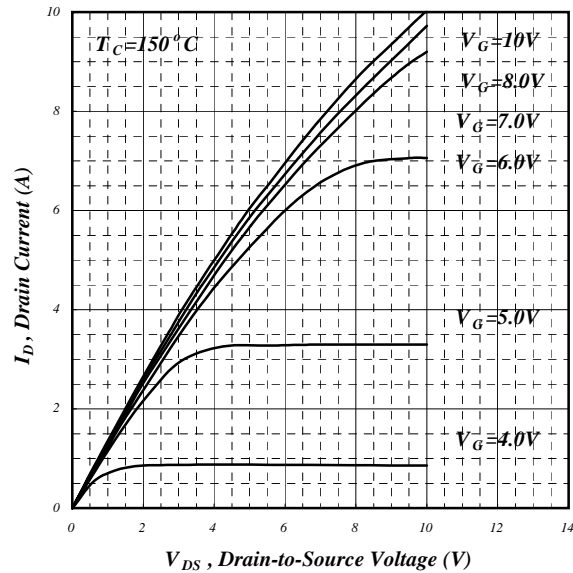


Fig 2. Typical Output Characteristics

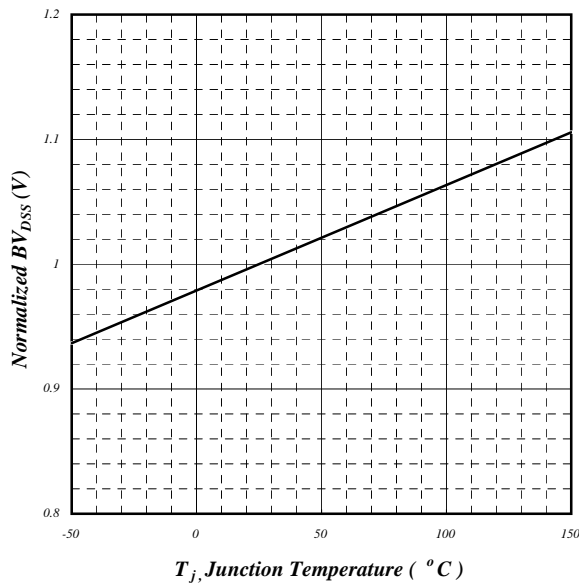


Fig 3. Normalized BV_{DSS} vs. Junction Temperature

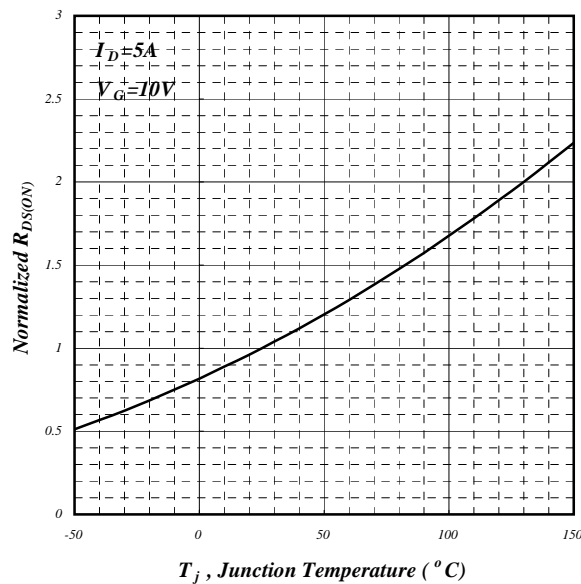


Fig 4. Normalized On-Resistance vs. Junction Temperature

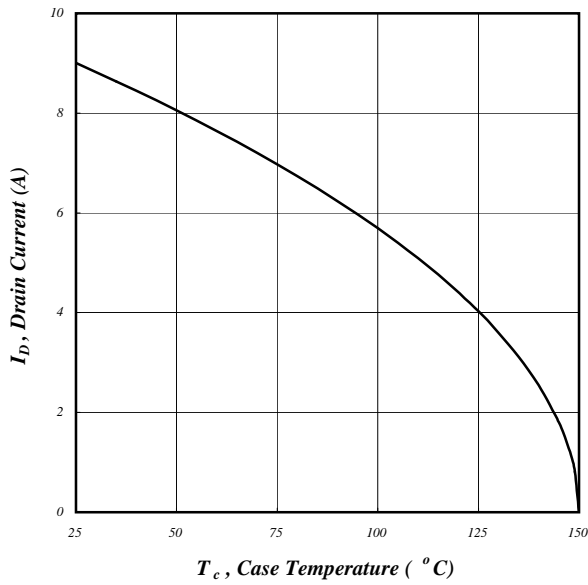


Fig 5. Maximum Drain Current vs. Case Temperature

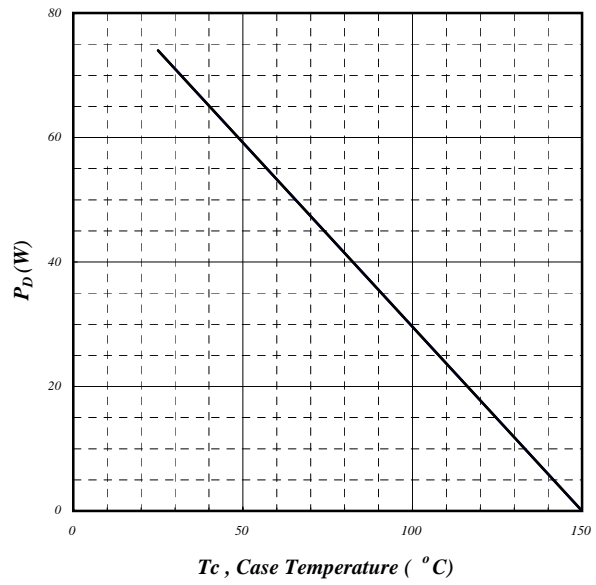


Fig 6. Typical Power Dissipation

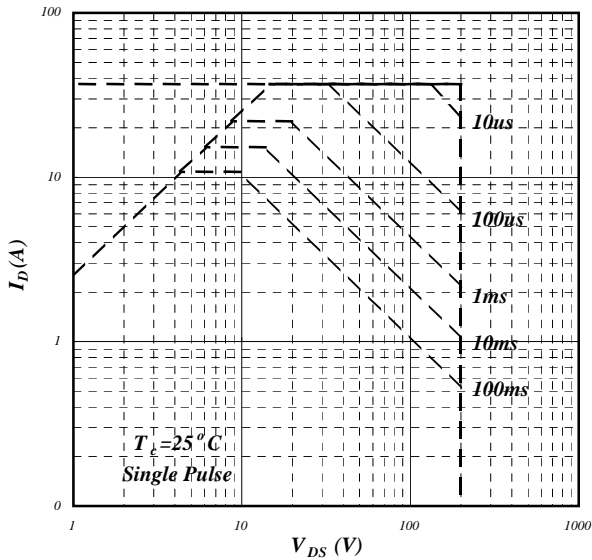


Fig 7. Maximum Safe Operating Area

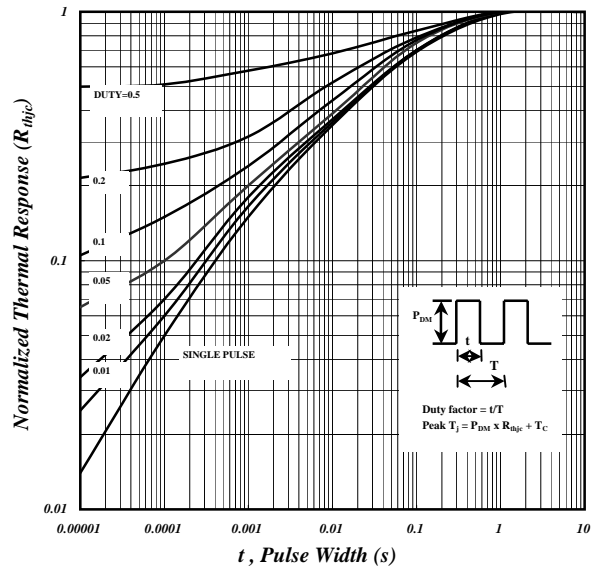


Fig 8. Effective Transient Thermal Impedance

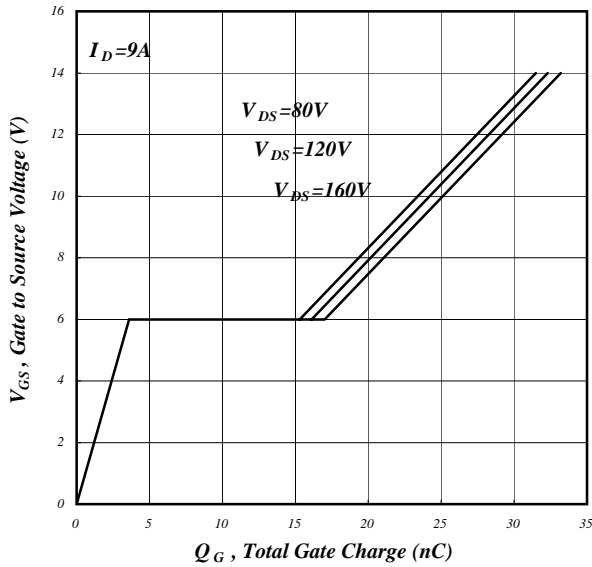


Fig 9. Gate Charge Characteristics

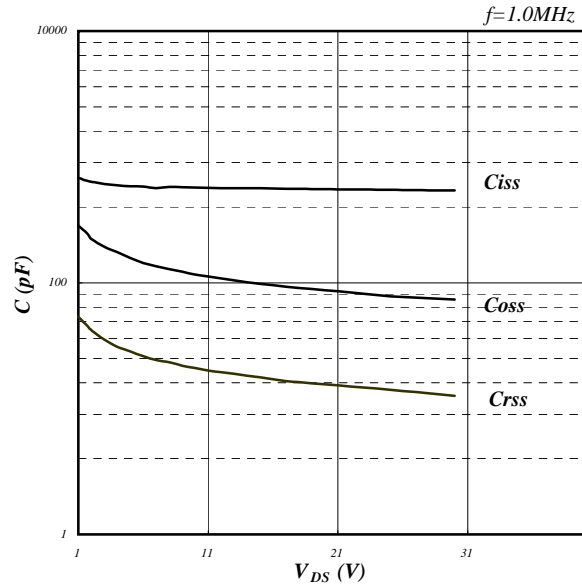


Fig 10. Typical Capacitance Characteristics

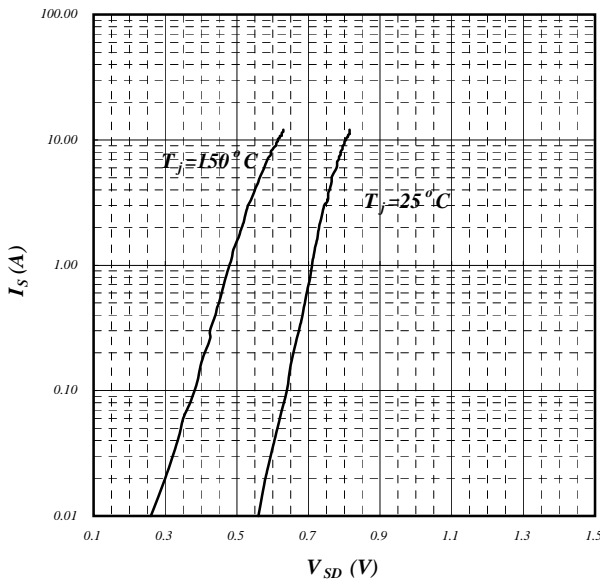


Fig 11. Forward Characteristic of Reverse Diode

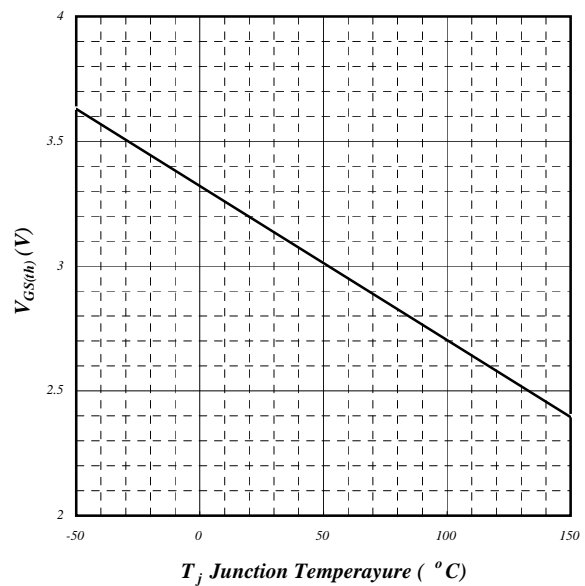


Fig 12. Gate Threshold Voltage vs. Junction Temperature

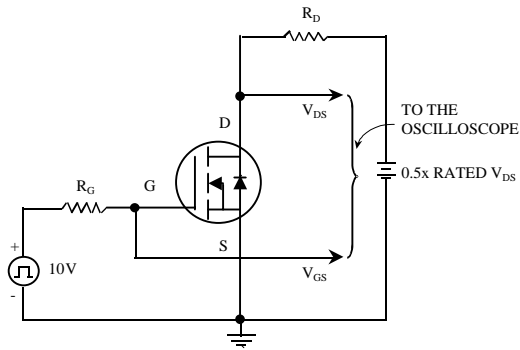


Fig 13. Switching Time Circuit

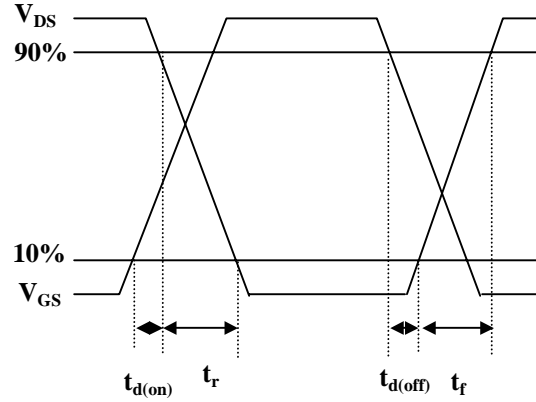


Fig 14. Switching Time Waveform

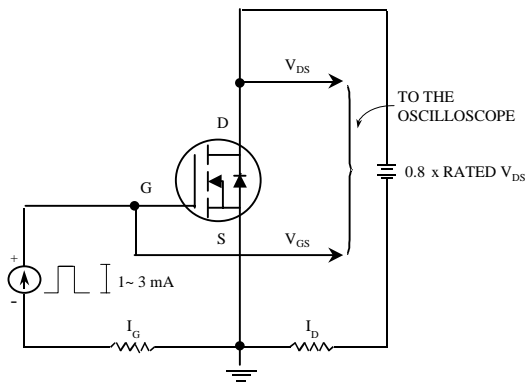


Fig 15. Gate Charge Circuit

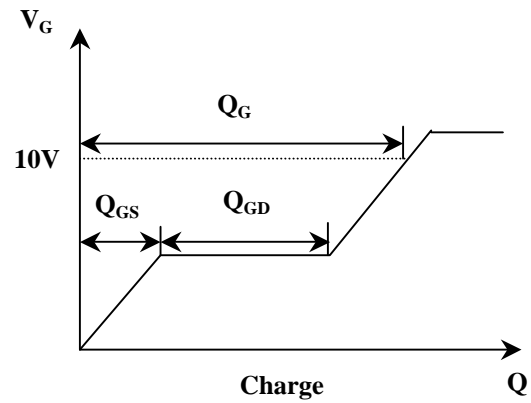
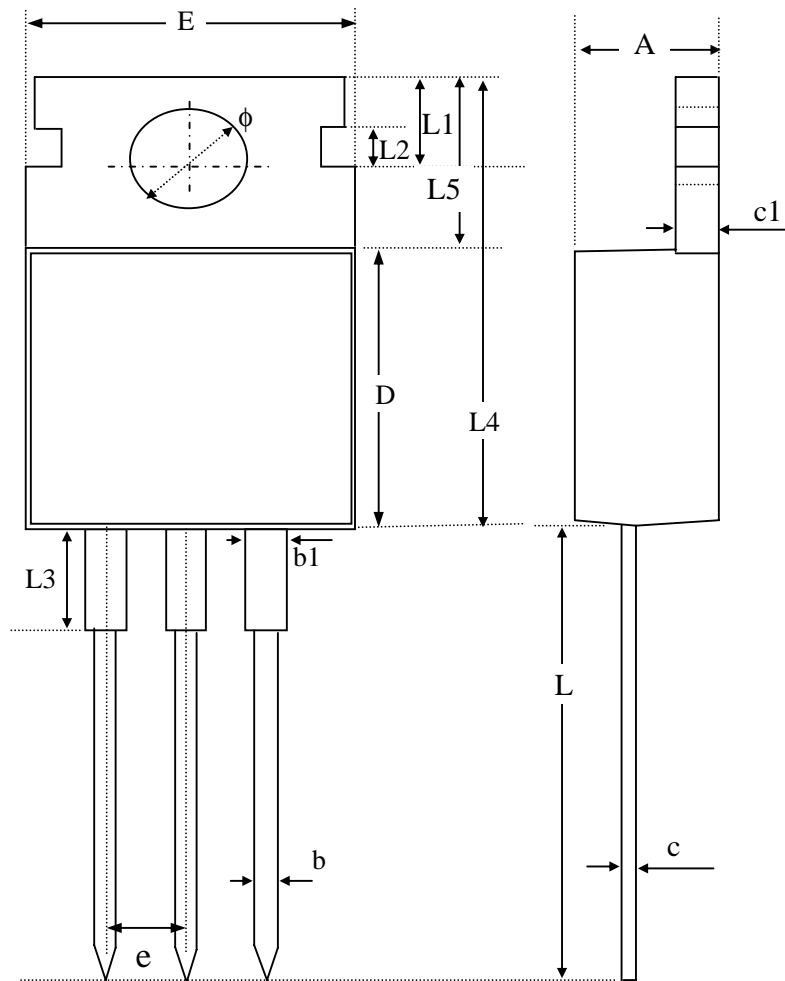


Fig 16. Gate Charge Waveform

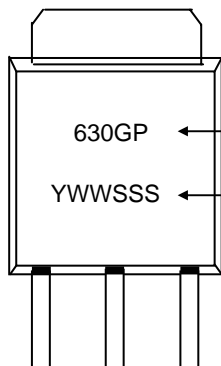
PHYSICAL DIMENSIONS - TO-220



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	4.25	4.48	4.70
b	0.65	0.80	0.90
b1	1.15	1.38	1.60
c	0.40	0.50	0.60
c1	1.00	1.20	1.40
E	9.70	10.00	10.40
e	----	2.54	----
L	12.70	13.60	14.50
L1	2.60	2.80	3.00
L2	1.00	1.40	1.80
L3	2.6	3.10	3.6
L4	14.70	15.50	16
L5	6.30	6.50	6.70
phi	3.50	3.60	3.70
D	8.40	8.90	9.40

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

PART MARKING - TO-220



PART NUMBER: 630GP = SSM630GP

DATE/LOT CODE:

Y = last digit of the year

WW = work week (01 -> 52)

SSS = lot code sequence

PACKING: Moisture sensitivity level MSL3

1000pcs in tubes packed inside a moisture barrier bag (MBB).

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